

## **KSA642**

## **Low Frequency Power Amplifier**

- Complement to KSD227
- Collector Power Dissipation: P<sub>C</sub> = 400mW
  Suffix "-C" means Center Collector (1. Emitter 2. Collector 3. Base)



### 1. Emitter 2. Base 3. Collector

## **PNP Epitaxial Silicon Transistor**

## **Absolute Maximum Ratings** $T_a$ =25°C unless otherwise noted

Symbol	Parameter	Ratings	Units
$V_{CBO}$	Collector-Base Voltage	-30	V
$V_{CEO}$	Collector-Emitter Voltage	-25	V
V <sub>EBO</sub>	Emitter-Base Voltage	-5	V
I <sub>C</sub>	Collector Current (DC)	-300	mA
I <sub>CP</sub>	* Collector Current (Pulse)	-500	mA
P <sub>C</sub>	Collector Power Dissipation	400	mW
TJ	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature	-55 ~ 150	°C

<sup>\*</sup> PW≤10ms, Duty cycle≤50%

### Electrical Characteristics T<sub>a</sub>=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV <sub>CBO</sub>	Collector-Base Breakdown Voltage	$I_C = -100 \mu A, I_E = 0$	-30			V
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = -10mA. I <sub>B</sub> =0	-25			V
BV <sub>EBO</sub>	Emitter-Base Breakdown Voltage	$I_E = -10\mu A. I_C = 0$	- 5			V
I <sub>CBO</sub>	Collector Cut-off Current	V <sub>CB</sub> = -25V, I <sub>E</sub> =0			-100	nA
I <sub>EBO</sub>	Emitter Cut-off Current	$V_{EB}$ = -3V, $I_{C}$ =0			-100	nA
h <sub>FE</sub>	* DC Current Gain	$V_{CE}$ = -1V, $I_{C}$ = -50mA	70		400	
V <sub>CE</sub> (sat)	* Collector-Emitter Saturation Voltage	$I_{C}$ = -300mA, $I_{B}$ = -30mA		-0.35	-0.6	V

<sup>\*</sup> Pulse Test: PW≤350μs, Duty cycle≤2%

## **h**<sub>FE</sub> Classification

Classification	0	Y	G
h <sub>FE</sub>	70 ~ 140	120 ~ 240	200 ~ 400

## **Typical Characteristics**

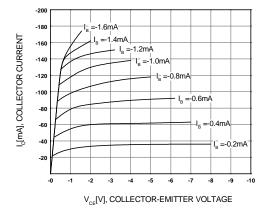


Figure 1. Static Characteristic

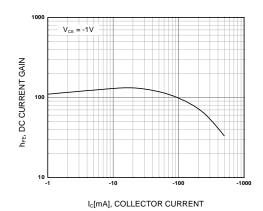


Figure 2. DC current Gain

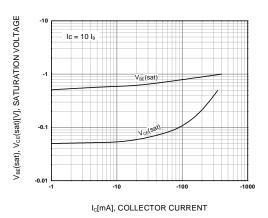


Figure 3. Base-Emitter Saturation Voltag Collector-Emitter Saturation Voltage

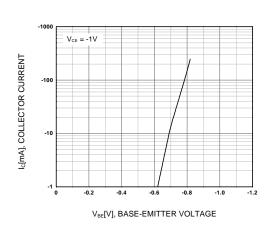


Figure 4. Base-Emitter On Voltage

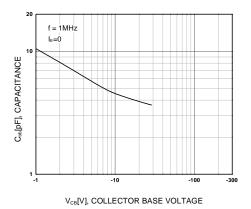
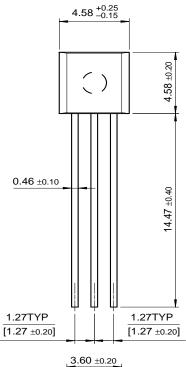


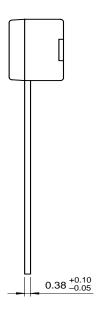
Figure 5. Collector Output Capacitance

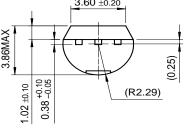
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# **Package Demensions**

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